

IGBT ECONO 3 Module, 100 A



ECONO 3, 4 pack

FEATURES

- Trench gate field stop IGBT
- 5 μ s short circuit capability
- Square RBSOA
- HEXFRED low Q_{rr} , low switching energy
- Positive $V_{CE(on)}$ temperature coefficient
- Copper baseplate
- Low stray inductance design
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

BENEFITS

- Benchmark efficiency for SMPS appreciation in particular HF welding
- Rugged transient performance
- Low EMI, requires less snubbing
- Direct mounting to heatsink space saving
- PCB solderable terminals
- Low junction to case thermal resistance

PRIMARY CHARACTERISTICS

V_{CES}	1200 V
$I_C(DC)$ at $T_C = 93^\circ C$	100 A
$V_{CE(on)}$ typ. at 100 A	2.12 V
Package	ECONO 3
Circuit configuration	4 pack with thermistor

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		1200	V
Continuous collector current	I_C	$T_C = 25\text{ }^{\circ}\text{C}$	170	A
		$T_C = 80\text{ }^{\circ}\text{C}$	115	
Pulsed collector current	I_{CM}		500	
Clamped inductive load current	I_{LM}		250	
Diode continuous forward current	I_F	$T_C = 25\text{ }^{\circ}\text{C}$	71	
		$T_C = 80\text{ }^{\circ}\text{C}$	49	
Diode maximum forward current	I_{FSM}		370	
Gate to emitter voltage	V_{GE}		± 20	V
Power dissipation IGBT	P_D	$T_C = 25\text{ }^{\circ}\text{C}$	595	W
		$T_C = 80\text{ }^{\circ}\text{C}$	333	
MODULE				
Operating junction temperature range	T_J		-40 to +150	$^{\circ}\text{C}$
Storage temperature range	T_{Stg}		-40 to +150	
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1\text{ s}$	3500	V

**ELECTRICAL SPECIFICATIONS** ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$, $I_C = 6\text{ mA}$	1200	-	-	
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$	-	1.8	-	V
		$V_{GE} = 15\text{ V}$, $I_C = 100\text{ A}$	-	2.12	2.43	
		$V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	1.88	-	
		$V_{GE} = 15\text{ V}$, $I_C = 100\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	2.35	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_C = 6\text{ mA}$	4.6	5.8	7.6	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$, $I_C = 6\text{ mA}$ ($25\text{ }^{\circ}\text{C}$ to $125\text{ }^{\circ}\text{C}$)	-	-12.3	-	mV/ $^{\circ}\text{C}$
Collector to emitter leaking current	I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = 1200\text{ V}$	-	1.1	75	μA
		$V_{GE} = 0\text{ V}$, $V_{CE} = 1200\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	0.72	-	mA
Diode forward voltage drop	V_{FM}	$I_F = 50\text{ A}$, $V_{GE} = 0\text{ V}$	-	2.59	3.15	V
		$I_F = 100\text{ A}$, $V_{GE} = 0\text{ V}$	-	3.38	-	
		$I_F = 50\text{ A}$, $V_{GE} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	2.69	-	
		$I_F = 100\text{ A}$, $V_{GE} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	3.74	-	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 750	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Total gate charge (turn-on)	Q _g	I _C = 100 A, V _{CC} = 960 V, V _{GE} = 15 V	-	455	-	nC	
Gate to emitter charge (turn-on)	Q _{ge}		-	51	-		
Gate to collector charge (turn-on)	Q _{gc}		-	211	-		
Turn-on switching loss	E _{on}	I _C = 100 A, V _{CC} = 600 V, V _{GE} = 15 V, R _g = 4.7 Ω, L = 500 μH, T _J = 25 °C	-	2.82	-	mJ	
Turn-off switching loss	E _{off}		-	3.47	-		
Total switching loss	E _{tot}		-	6.29	-		
Turn-on switching loss	E _{on}	I _C = 100 A, V _{CC} = 600 V, V _{GE} = 15 V, R _g = 4.7 Ω, L = 500 μH, T _J = 125 °C	-	4.09	-	mJ	
Turn-off switching loss	E _{off}		-	5.67	-		
Total switching loss	E _{tot}		-	9.76	-		
Turn-on delay time	t _{d(on)}	I _C = 100 A, V _{CC} = 600 V, V _{GE} = 15 V, R _g = 4.7 Ω, L = 500 μH, T _J = 125 °C	-	63	-	ns	
Rise time	t _r		-	28	-		
Turn-off delay time	t _{d(off)}		-	222	-		
Fall time	t _f		-	150	-		
Reverse bias safe operating area	RBSOA	T _J = 150 °C, I _C = 250 A, V _{GE} = 15 V to 0 V, R _g = 4.7 Ω, V _{CC} = 700 V, V _p = 1200 V	Full square				
Short circuit safe operating area	SCSOA	V _{CC} = 600 V, V _{GE} = 15 V, T _J = 150 °C	-	-	5	μs	
Diode reverse recovery time	t _{rr}	I _F = 50 A, dI _F /dt = 200 A/μs, V _R = 400 V	T _J = 25 °C	-	190	-	ns
			T _J = 125 °C	-	293	-	
Diode peak reverse current	I _{rr}		T _J = 25 °C	-	12	-	A
			T _J = 125 °C	-	18.6	-	
Diode recovery charge	Q _{rr}	T _J = 25 °C	-	1140	-	nC	
		T _J = 125 °C	-	2725	-		

**INTERNAL NTC - THERMISTOR SPECIFICATIONS**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUE	UNITS
Resistance	R ₂₅	T _C = 25 °C	5000	Ω
	R ₁₀₀	T _C = 100 °C	493 ± 5 %	
B-value	B _{25/50}	R ₂ = R ₂₅ exp. [B _{25/50} (1/T ₂ - 1/(298.15 K))]	3375 ± 5 %	K
Maximum operating temperature			220	°C
Dissipation constant			2	mW/°C
Thermal time constant			8	s

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
IGBT - junction-to-case (per switch)	R _{thJC}	-	-	0.21	°C/W
DIODE - junction-to-case (per diode)	R _{thJC}	-	-	0.46	
Case to sink, flat, greased surface (per module)	R _{thJS}	-	0.015	-	
Mounting torque (M5)		3.0	-	6.0	Nm
Weight		-	285	-	g

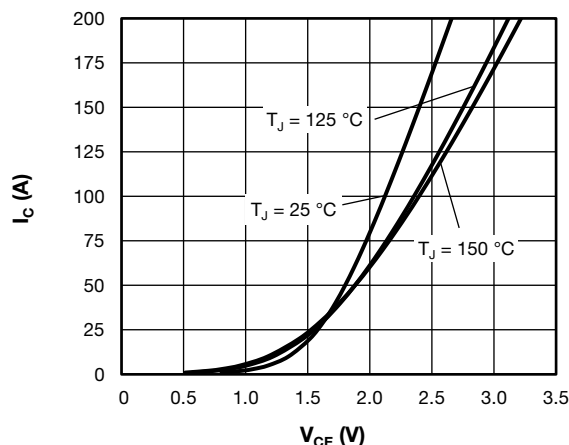
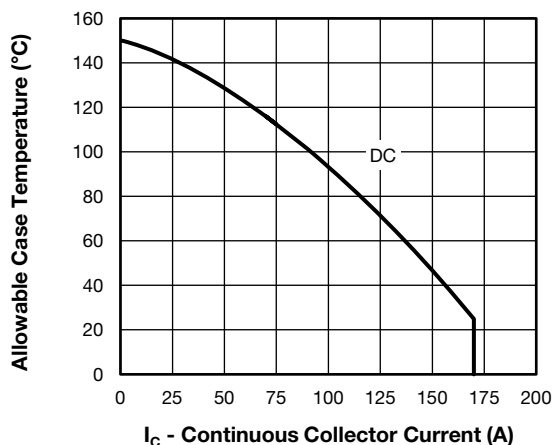
Fig. 1 - Typical Trench IGBT Output Characteristics, V_{GE} = 15 V

Fig. 3 - Maximum Trench IGBT Continuous Collector Current vs. Case Temperature

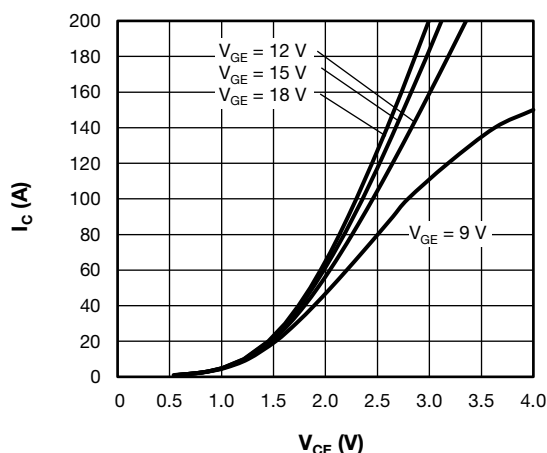
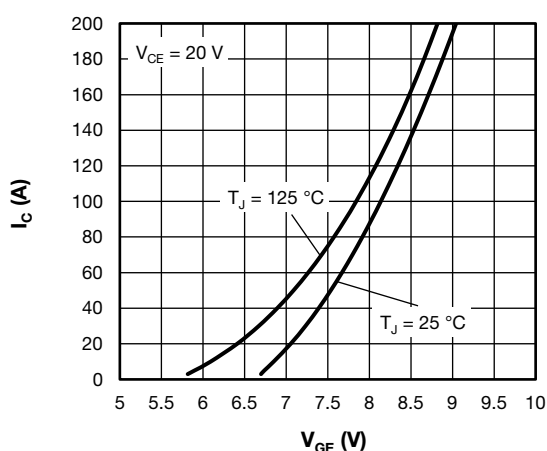
Fig. 2 - Typical Trench IGBT Output Characteristics, T_J = 125 °C

Fig. 4 - Typical Trench IGBT Transfer Characteristics

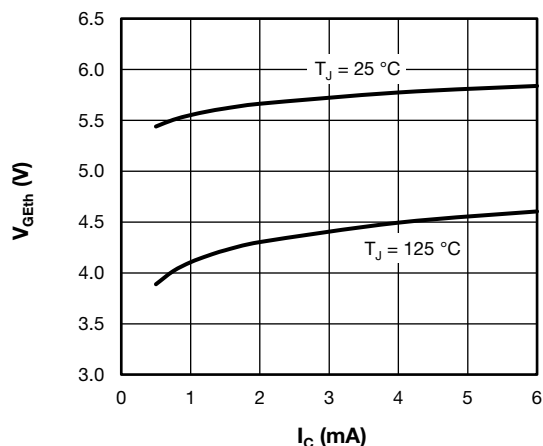
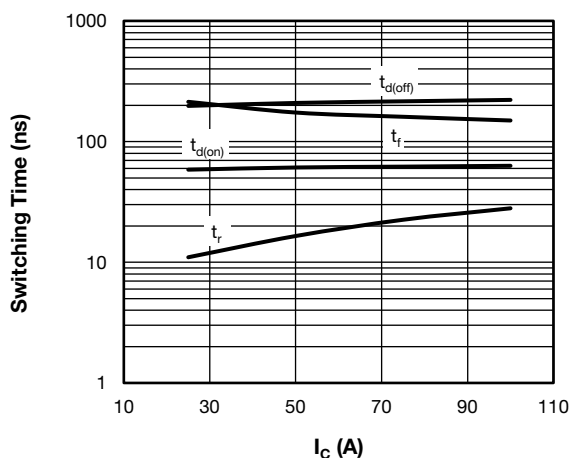


Fig. 5 - Typical Trench IGBT Gate Threshold Voltage


Fig. 8 - Typical Trench IGBT Switching Time vs. I_C with (Antiparallel Diode)

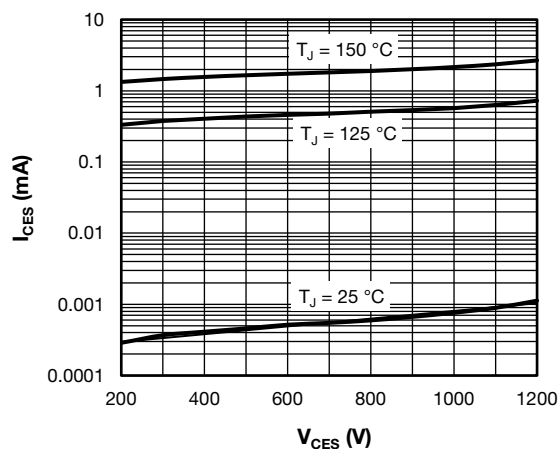
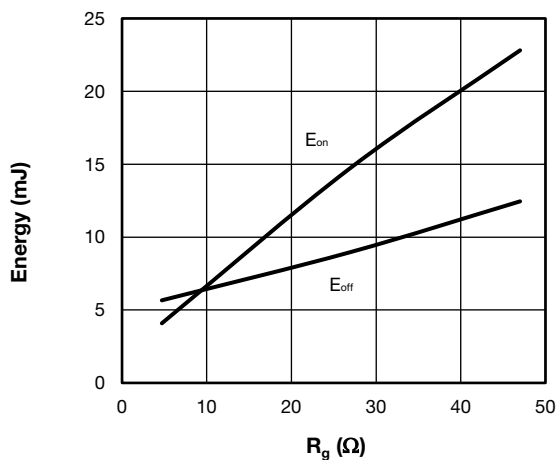
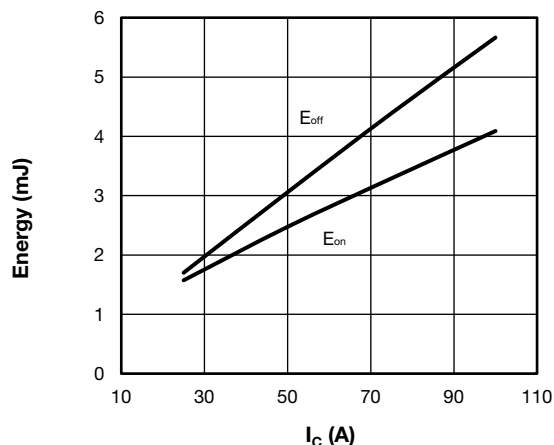
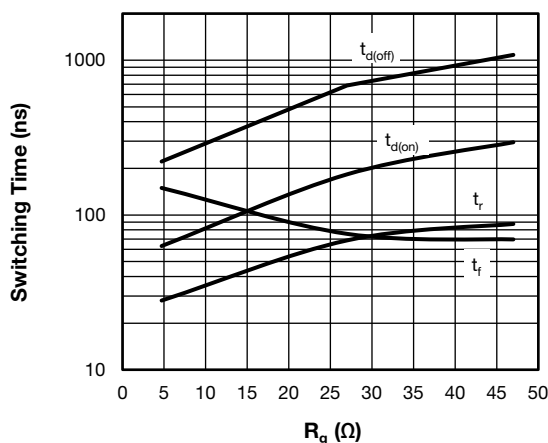
 $T_J = 125^\circ\text{C}$, $V_{CC} = 600\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$


Fig. 6 - Typical Trench IGBT Zero Gate Voltage Collector Current


Fig. 9 - Typical Trench IGBT Energy Loss vs. R_g with (Antiparallel Diode)

 $T_J = 125^\circ\text{C}$, $V_{CC} = 600\text{ V}$, $I_C = 100\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

Fig. 7 - Typical IGBT Energy Loss vs. I_C with (Antiparallel Diode)

 $T_J = 125^\circ\text{C}$, $V_{CC} = 600\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

Fig. 10 - Typical Trench IGBT Switching Time vs. R_g with (Antiparallel Diode)

 $T_J = 125^\circ\text{C}$, $V_{CC} = 600\text{ V}$, $I_C = 100\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

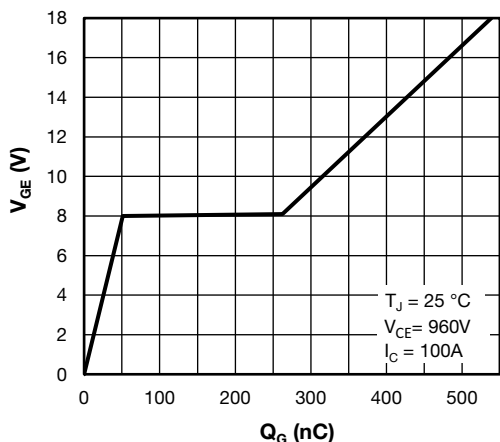


Fig. 11 - Typical Trench IGBT Gate Charge vs. Gate to Emitter Voltage

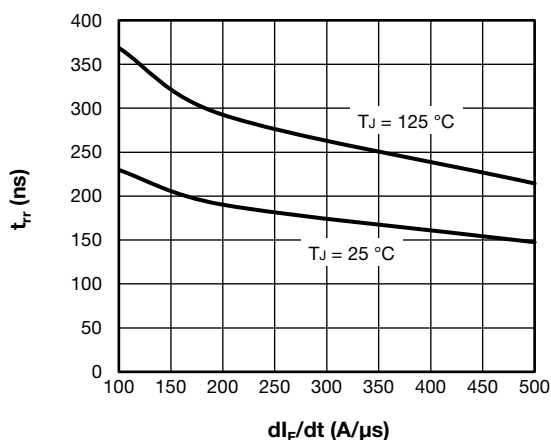


Fig. 14 - Typical Diode Reverse Recovery Time vs. dI_F/dt
 $V_{rr} = 400\text{ V}$, $I_F = 50\text{ A}$

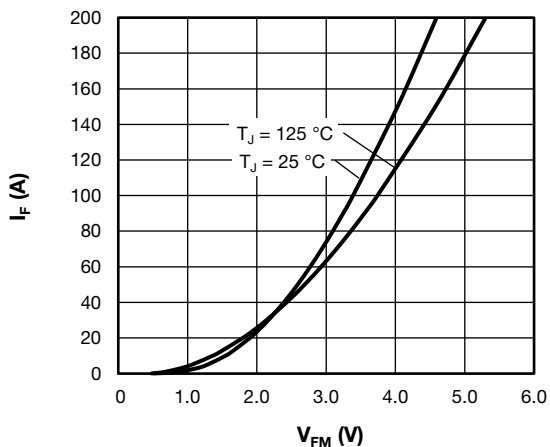


Fig. 12 - Typical Diode Forward Characteristics

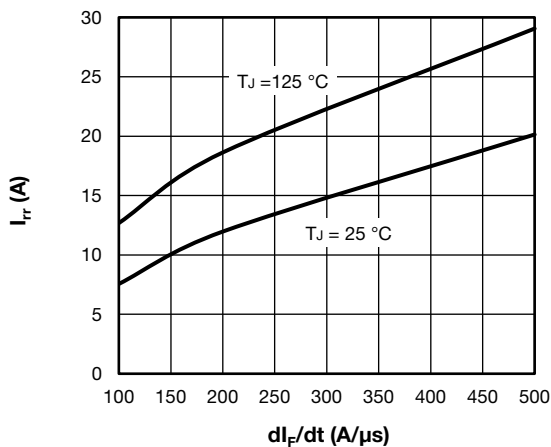


Fig. 15 - Typical Diode Reverse Recovery Current vs. dI_F/dt
 $V_{rr} = 400\text{ V}$, $I_F = 50\text{ A}$

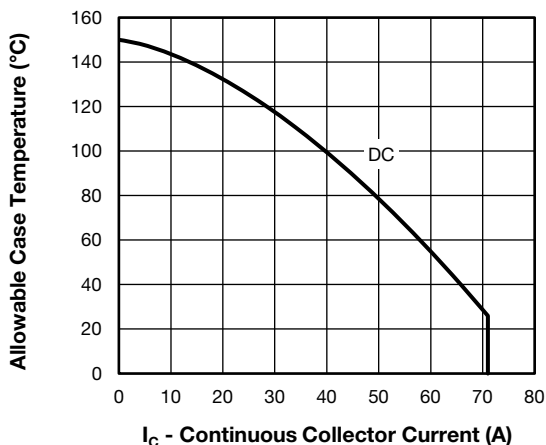


Fig. 13 - Maximum Diode Continuous Forward Current vs. Case Temperature

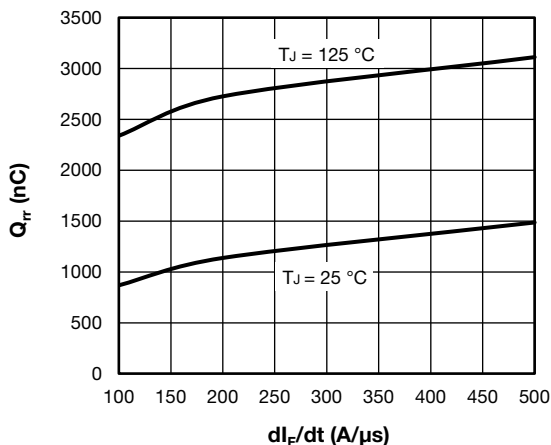


Fig. 16 - Typical Diode Reverse Recovery Charge vs. dI_F/dt
 $V_{rr} = 400\text{ V}$, $I_F = 50\text{ A}$

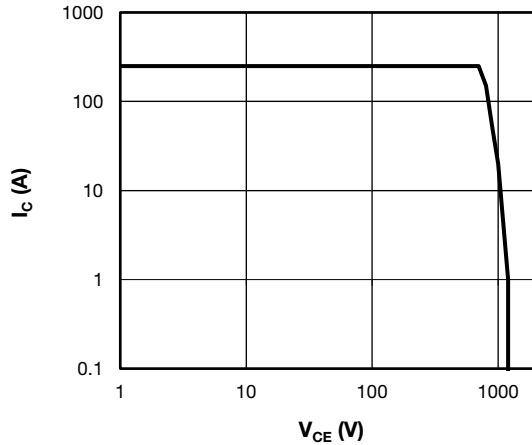


Fig. 17 - Trench IGBT Reverse BIAS SOA
 $T_J = 150^\circ\text{C}$, $I_C = 200\text{ A}$, $R_{\theta} = 10^\circ\text{C/W}$, $V_{GE} = +15\text{ V/0 V}$,
 $V_{CC} = 600\text{ V}$, $V_p = 1200\text{ V}$

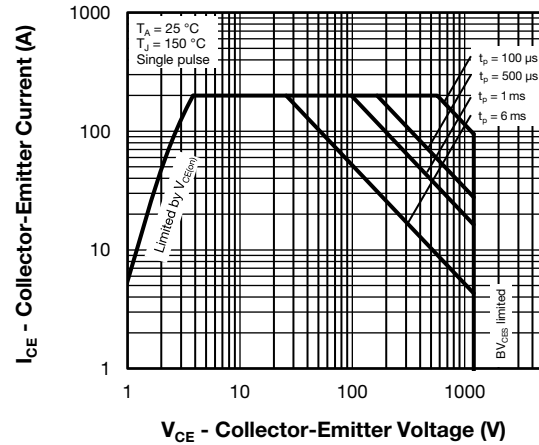


Fig. 18 - Trench IGBT Safe Operating Area

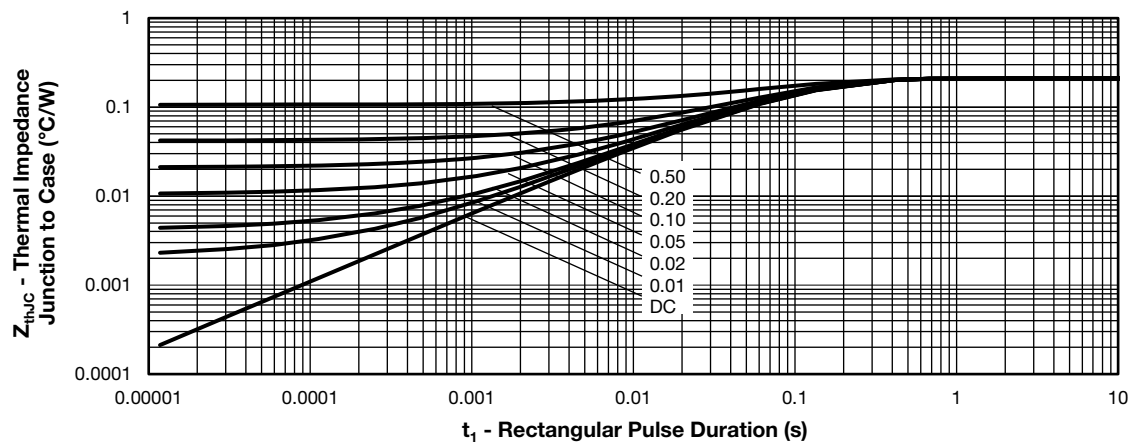


Fig. 19 - Maximum Trench IGBT Thermal Impedance Z_{thJC} Characteristics

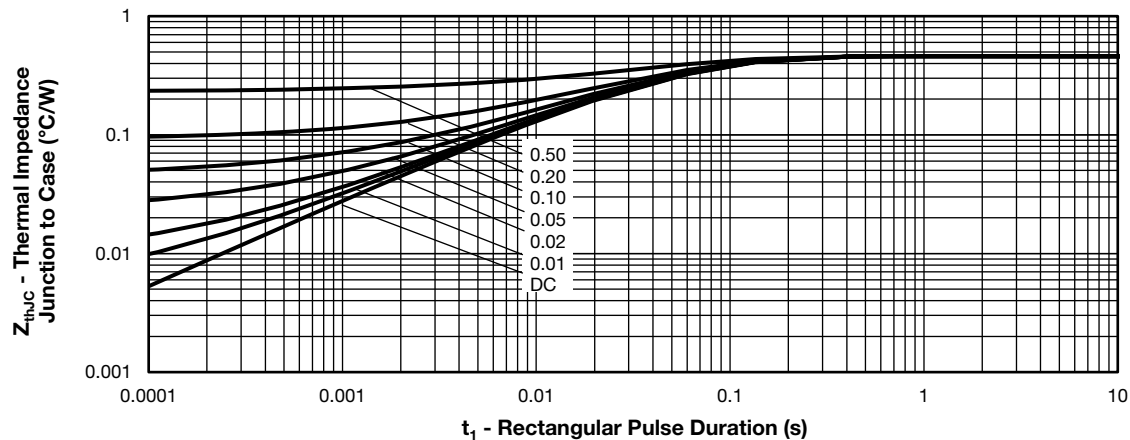


Fig. 20 - Maximum Diode Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code	VS-	G	T	100	Y	G	120	U	T
	1	2	3	4	5	6	7	8	9

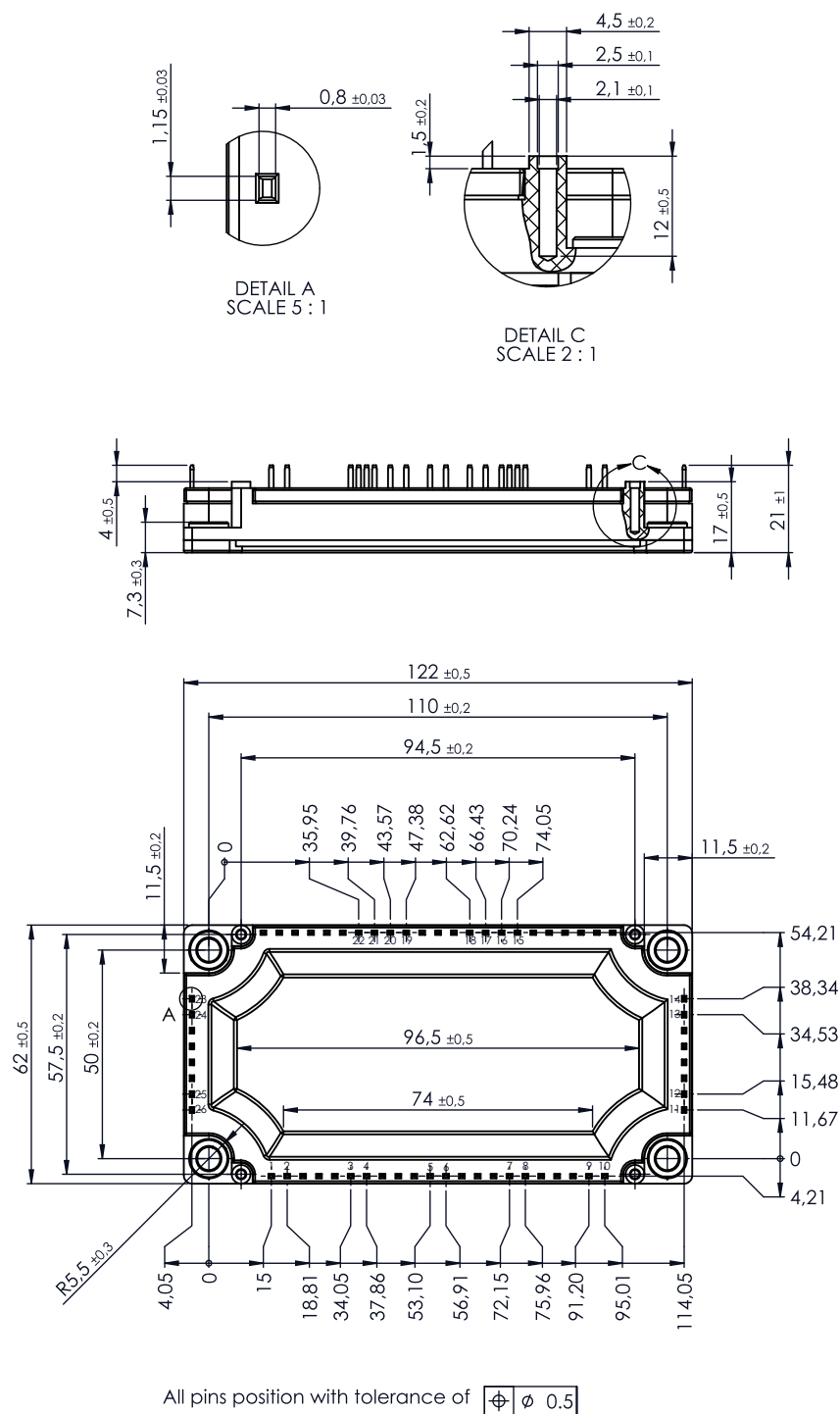
- 1** - Vishay Semiconductors product
- 2** - Insulated gate bipolar transistor (IGBT)
- 3** - T = Trench IGBT technology
- 4** - Current rating (100 = 100 A)
- 5** - Circuit configuration (Y = 4 pack)
- 6** - Package indicator (G = ECONO 3)
- 7** - Voltage rating (120 = 1200 V)
- 8** - Speed / type (U = Ultrafast IGBT)
- 9** - NTC thermistor

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
4 pack with thermistor	Y	

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95686

ECONO3 4 Pack

DIMENSIONS in millimeters and inches





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